

Vishay Semiconductors

AUTOMOTIVE

RoHS

COMPLIANT HALOGEN

FREE

Ultrafast Rectifier, 2 A FRED Pt®

eSMP[®] Series





Top View Bottom View

MicroSMP (DO-219AD)

Anode O Cathode

LINKS TO ADDITIONAL RESOURCES



| PRIMARY CHARACTERISTICS | | | | |
|----------------------------------|---------------------|--|--|--|
| I _{F(AV)} | 2 A | | | |
| V _R | 100 V, 200 V | | | |
| V _F at I _F | 0.82 V | | | |
| t _{rr} (typ.) | 33 ns | | | |
| I _{FSM} | 30 A | | | |
| T _J max. | 175 °C | | | |
| Package | MicroSMP (DO-219AD) | | | |
| Circuit configuration | Single | | | |

FEATURES

- Very low profile typical height of 0.65 mm
- · Ideal for automated placement
- · Low forward voltage drop, low power losses
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- For PFC, CRM snubber operation
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

For use in high frequency, freewheeling, DC/DC converters, PFC, and in snubber industrial and automotive applications.

MECHANICAL DATA

Case: MicroSMP (DO-219AD)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per

J-STD-002, meets JESD 201 class 2 whisker test

Polarity: color band denotes cathode end

| ABSOLUTE MAXIMUM RATINGS | | | | | | | |
|----------------------------------------------|-----------------------------------|---------------------------------|-------------|-------|--|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | | |
| Peak repetitive reverse voltage VS-2EQH01HM3 | - V _{RRM} | | 100 | V | | | |
| VS-2EQH02HM3 | | | 200 | | | | |
| Average rectified forward current | I _{F(AV)} | T _M = 137 °C | 2 | ۸ | | | |
| Non-repetitive peak surge current | I _{FSM} | $T_J = 25$ °C, 10 ms sine pulse | 30 | A | | | |
| Operating junction and storage temperatures | T _J , T _{Stg} | | -55 to +175 | °C | | | |

| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | | |
|--------------------------------------------------------------------------------------|----------------|----------------------|--------------------------------------------------------|------|------|------|-------|
| PARAMETER | | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Breakdown voltage, | VS-2EQH01HM3 | V_{BR} , | I _R = 100 μA | 100 | - | - | |
| blocking voltage | VS-2EQH02HM3 | V_R | | 200 | | | V |
| Farmer de la la cara | V | I _F = 2 A | - | 0.96 | 1.05 | V | |
| Forward voltage | orward voltage | V _F | I _F = 2 A, T _J = 150 °C | - | 0.82 | 0.84 | |
| Reverse leakage current | | , | V _R = V _R rated | - | - | 1 | |
| | | IR | $T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$ | - | - | 25 | μA |
| Junction capacitance | | C _T | V _R = 200 V | - | 6 | - | pF |

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| DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified) | | | | | | | |
|---------------------------------------------------------------------------------------------|-------------------------|-------------------------------------------------------------------------------|----------------------|------|------|------|---------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNITS |
| | | $I_F = 1.0 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$ | | - | 33 | - | |
| Reverse recovery time t _{rr} | | I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A | | - | - | 23 | |
| | ιm | T _J = 25 °C | I _F = 2 A | - | 19 | - | ns A |
| | | T _J = 125 °C | | - | 33 | - | |
| Peak recovery current I _{RRM} | , | T _J = 25 °C | | - | 1.7 | - | |
| | T _J = 125 °C | $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 100 \text{ V}$ | - | 2.5 | - | _ ^ | |
| Reverse recovery charge Q _{rr} | T _J = 25 °C | | - | 15 | - | nC | |
| | T _J = 125 °C | | - | 34 | - | TIC | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | | |
|-----------------------------------------|---------------------|-----------------------------------|-----------------------------------------------------|------|-------|------|-------|
| PARAMETER | | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Maximum junction and range | storage temperature | T _J , T _{Stg} | | -55 | - | 175 | °C |
| Thermal resistance, junction to mount | | R _{thJM} ⁽¹⁾ | | - | 16 | 20 | |
| Thermal resistance, junction to ambient | | R _{thJA} | Device mounted on FR4 PCB, 2 oz. standard footprint | - | 160 | - | °C/W |
| Approximate weight | | | | | 0.006 | | g |
| Marking device | VS-2EQH01HM3 | | Case style MicroSMP (DO-219AD) | 2H1 | | | • |
| iviai kirig device | VS-2EQH02HM3 | | Case style MicrosMP (DO-219AD) | | 2H2 | | • |

Note

⁽¹⁾ Thermal resistance junction to mount follows JEDEC® 51-14 transient dual interface test method (TDIM)

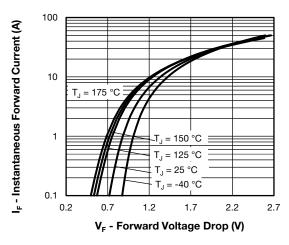


Fig. 1 - Typical Forward Voltage Drop Characteristics

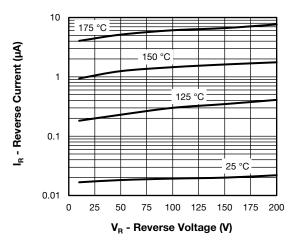


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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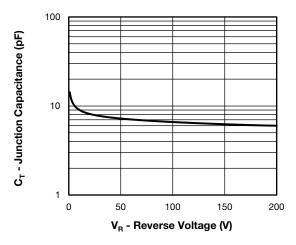


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

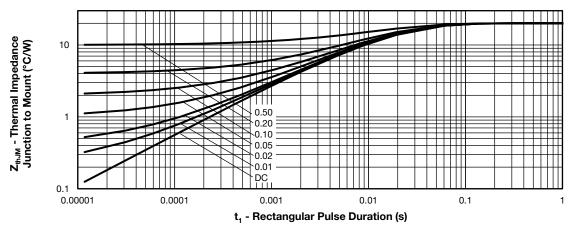


Fig. 4 - Maximum Transient Thermal Impedance, Junction to Mount

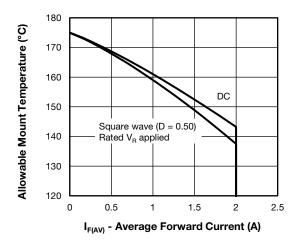


Fig. 5 - Maximum Allowable Mount Temperature vs. Average Forward Current

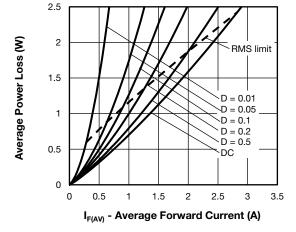
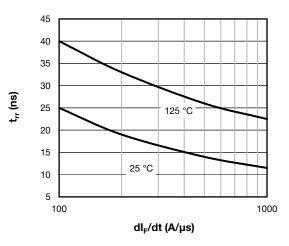


Fig. 6 - Forward Power Loss Characteristics

Note

Formula used: $T_M = T_J - (Pd + Pd_{REV}) \times R_{thJM}$; $Pd = forward power loss = I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 5); $Pd_{REV} = inverse power loss = V_{R1} \times I_R$ (1 - D); I_R at $V_{R1} = rated V_R$

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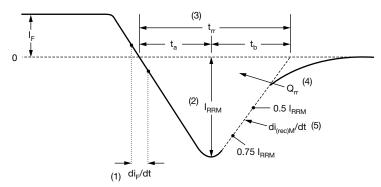


45 40 35 30 35 25 20 15 100 1000 dl_F/dt (A/μs)

50

Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

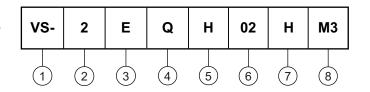
(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (2 = 2 A)

- Circuit configuration:

E = single diode

4 - Q = MicroSMP package

5 - Process type,

H = ultrafast recovery

6 - Voltage code (02 = 200 V)

7 - H = AEC-Q101 qualified

8 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

| ORDERING INFORMATION (Example) | | | | | | |
|-----------------------------------------------------------------------------------|---|------|-----------------------------------|--|--|--|
| PREFERRED P/N PREFERRED PACKAGE CODE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION | | | | | | |
| VS-2EQH01HM3/H | Н | 4500 | 7" diameter plastic tape and reel | | | |
| VS-2EQH02HM3/H | Н | 4500 | 7" diameter plastic tape and reel | | | |

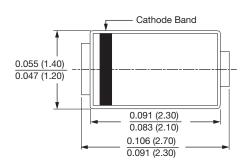
| LINKS TO RELATED DOCUMENTS | | | | |
|--------------------------------------------|--------------------------|--|--|--|
| Dimensions <u>www.vishay.com/doc?96591</u> | | | | |
| Part marking information | www.vishay.com/doc?96590 | | | |
| Packaging information | www.vishay.com/doc?88869 | | | |
| SPICE model | www.vishay.com/doc?96595 | | | |

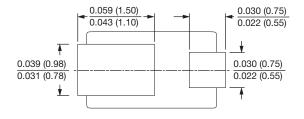


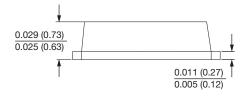
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MicroSMP (DO-219AD), FRED Pt®

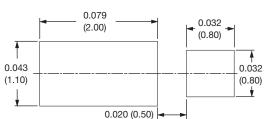
DIMENSIONS in inches (millimeters)







Mounting Pad Layout





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